Discrete POWER & Signal **Technologies**

2N5961



2N5961



NPN General Purpose Amplifier

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Val60ue	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage 8.0		V
I _C	Collector Current - Continuous	100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

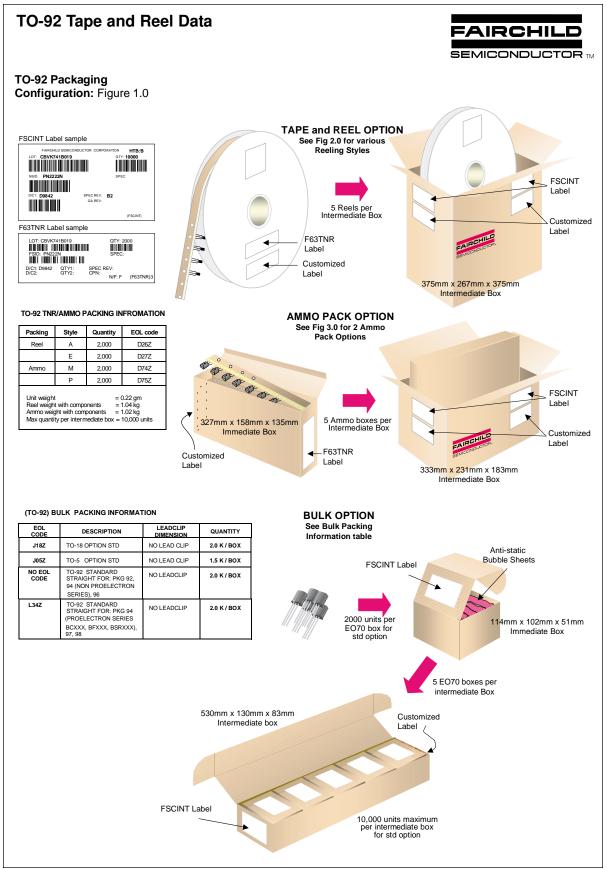
Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		2N5961		
PD	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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NPN General Purpose Amplifier (continued)

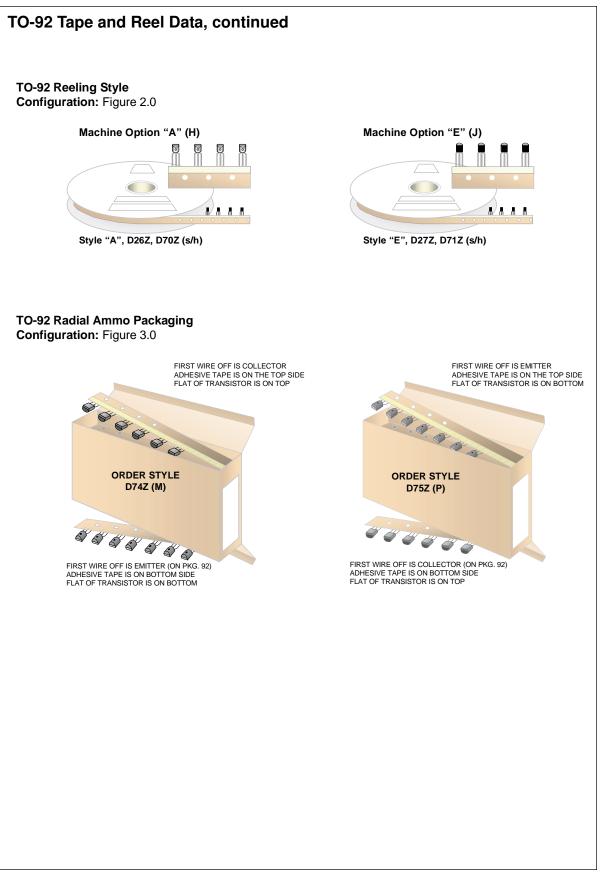
Symbol	Parameter	Test Conditions	Min	Max	Units
	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 5.0 \text{ mA}, I_{\rm B} = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	8.0		V
сво	Collector Cutoff Current			2.0 50	nA nA
EBO	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		1.0	nA
/ _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	135 150	700 0.2	V
		$V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A}$ $V_{CE} = 5.0 \text{ V}, I_C = 1.0 m\text{A}$	120 135		
1	Collector Emitter Seturation Voltage		150		V
VCE(sat)		$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.3$ mA $I_{\rm C} = 10$ mA, $I_{\rm B} = 1.0$ mA		0.2	V
V _{BE(on)}	Base-Emitter On Voltage	$V_{cE} = 5.0 \text{ V}, I_c = 1.0 \text{ mA}$	0.5	0.7	V
SMALL S C _{cb} C _{eb} Pre	IGNAL CHARACTERISTICS Collector-Base Capacitance Emitter-Base Capacitance Small-Signal Current Gain	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$ $V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$	150	4.0 6.0 1000	pF pF
NF	Noise Figure	$\begin{split} & V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ & R_{S} = 10 k\Omega, f = 1.0 \text{kHz}, \\ & B_{W} = 400 \text{Hz} \\ & V_{CE} = 5.0 \text{V}, \text{ I}_{C} = 10 \mu\text{A}, \\ & R_{S} = 10 k\Omega, f = 10 \text{Hz} - 10 \text{kHz} \\ & B_{W} = 15.7 \text{kHz} \\ & V_{CE} = 5.0 \text{V}, \text{ I}_{C} = 100 \mu\text{A}, \\ & R_{S} = 1.0 \text{k}\Omega, f = 1.0 \text{kHz} \\ & B_{W} = 400 \text{Hz} \end{split}$	1.0	3.0 3.0 6.0	dB dB dB

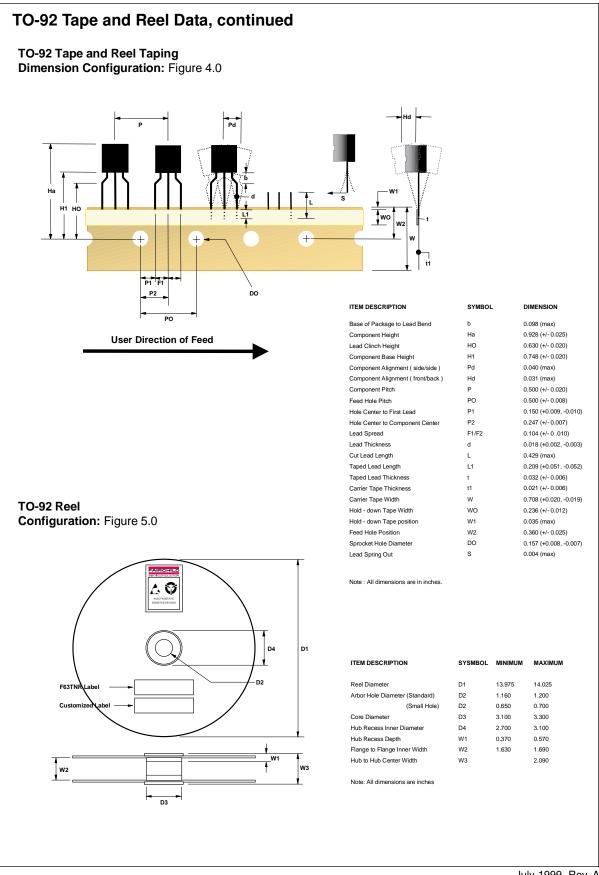
2N5961



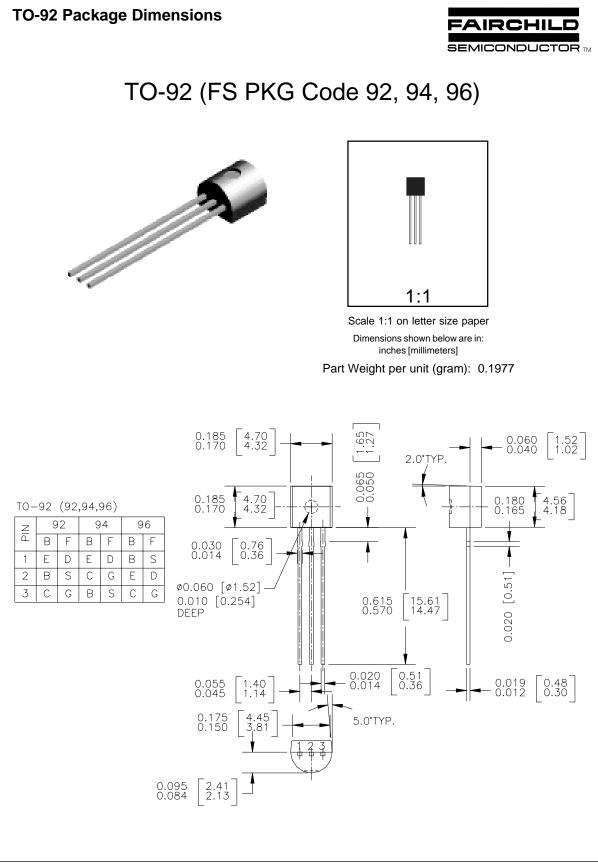
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